

# Mingxing Wang

## List of Publications by Citations

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#	Paper	IF	Citations
274	X-ray photoelectron spectroscopy and auger electron spectroscopy studies of Al-doped ZnO films. <i>Applied Surface Science</i> , <b>2000</b> , 158, 134-140	6.7	1089
273	Generation and electric control of spin-valley-coupled circular photogalvanic current in WSe <sub>2</sub> . <i>Nature Nanotechnology</i> , <b>2014</b> , 9, 851-7	28.7	216
272	Robustness of topological order and formation of quantum well states in topological insulators exposed to ambient environment. <i>Proceedings of the National Academy of Sciences of the United States of America</i> , <b>2012</b> , 109, 3694-8	11.5	139
271	Molecular beam epitaxy growth of GaN, AlN and InN. <i>Progress in Crystal Growth and Characterization of Materials</i> , <b>2004</b> , 48-49, 42-103	3.5	134
270	Nitrogen doped ZnO film grown by the plasma-assisted metal-organic chemical vapor deposition. <i>Journal of Crystal Growth</i> , <b>2001</b> , 226, 123-129	1.6	114
269	Polarity and Its Influence on Growth Mechanism during MOVPE Growth of GaN Sub-micrometer Rods. <i>Crystal Growth and Design</i> , <b>2011</b> , 11, 1573-1577	3.5	102
268	Proposal and achievement of novel structure InN/GaN multiple quantum wells consisting of 1 ML and fractional monolayer InN wells inserted in GaN matrix. <i>Applied Physics Letters</i> , <b>2007</b> , 90, 073101	3.4	102
267	X-ray photoelectron spectroscopy study of ZnO films grown by metal-organic chemical vapor deposition. <i>Journal of Crystal Growth</i> , <b>2003</b> , 252, 180-183	1.6	93
266	High-quality AlN epitaxy on nano-patterned sapphire substrates prepared by nano-imprint lithography. <i>Scientific Reports</i> , <b>2016</b> , 6, 35934	4.9	92
265	Physical origin of Davydov splitting and resonant Raman spectroscopy of Davydov components in multilayer MoTe <sub>2</sub> . <i>Physical Review B</i> , <b>2016</b> , 93,	3.3	77
264	High-Electron-Mobility InN Layers Grown by Boundary-Temperature-Controlled Epitaxy. <i>Applied Physics Express</i> , <b>2012</b> , 5, 015502	2.4	77
263	Crystal growth of undoped ZnO films on Si substrates under different sputtering conditions. <i>Journal of Crystal Growth</i> , <b>2002</b> , 243, 439-443	1.6	74
262	Effect of post-thermal annealing on properties of ZnO thin film grown on c-Al <sub>2</sub> O <sub>3</sub> by metal-organic chemical vapor deposition. <i>Journal of Crystal Growth</i> , <b>2003</b> , 252, 275-278	1.6	69
261	Phonon lifetimes and phonon decay in InN. <i>Applied Physics Letters</i> , <b>2005</b> , 86, 223501	3.4	68
260	Polarity control of ZnO films grown on nitrided c-sapphire by molecular-beam epitaxy. <i>Applied Physics Letters</i> , <b>2005</b> , 86, 011921	3.4	68
259	Threading dislocations in In-polar InN films and their effects on surface morphology and electrical properties. <i>Applied Physics Letters</i> , <b>2007</b> , 90, 151901	3.4	64
258	Effect of epitaxial temperature on N-polar InN films grown by molecular beam epitaxy. <i>Journal of Applied Physics</i> , <b>2006</b> , 99, 073512	2.5	62

257	Step-Flow Growth of In-Polar InN by Molecular Beam Epitaxy. <i>Japanese Journal of Applied Physics</i> , <b>2006</b> , 45, L730-L733	1.4	61
256	Systematic study on p-type doping control of InN with different Mg concentrations in both In and N polarities. <i>Applied Physics Letters</i> , <b>2007</b> , 91, 242111	3.4	60
255	Growth and properties of Mg-doped In-polar InN films. <i>Applied Physics Letters</i> , <b>2007</b> , 90, 201913	3.4	57
254	Hole mobility in Mg-doped p-type InN films. <i>Applied Physics Letters</i> , <b>2008</b> , 92, 132108	3.4	55
253	High-Output-Power Ultraviolet Light Source from Quasi-2D GaN Quantum Structure. <i>Advanced Materials</i> , <b>2016</b> , 28, 7978-7983	2.4	54
252	Experimental determination of strain-free Raman frequencies and deformation potentials for the E2 high and A1(LO) modes in hexagonal InN. <i>Applied Physics Letters</i> , <b>2006</b> , 89, 171907	3.4	49
251	Efficient silicon quantum dots light emitting diodes with an inverted device structure. <i>Journal of Materials Chemistry C</i> , <b>2016</b> , 4, 673-677	7.1	48
250	Epitaxial growth of AlN films on sapphire via a multilayer structure adopting a low- and high-temperature alternation technique. <i>CrystEngComm</i> , <b>2015</b> , 17, 7496-7499	3.3	46
249	Recent advances and challenges for successful p-type control of InN films with Mg acceptor doping by molecular beam epitaxy. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2010</b> , 207, 1011-1023	1.6	45
248	Identification of helicity-dependent photocurrents from topological surface states in Bi <sub>2</sub> Se <sub>3</sub> gated by ionic liquid. <i>Scientific Reports</i> , <b>2014</b> , 4, 4889	4.9	44
247	Fabrication and characterization of novel monolayer InN quantum wells in a GaN matrix. <i>Journal of Vacuum Science &amp; Technology B</i> , <b>2008</b> , 26, 1551		44
246	The discrepancies between theory and experiment in the optical emission of monolayer In(Ga)N quantum wells revisited by transmission electron microscopy. <i>Applied Physics Letters</i> , <b>2014</b> , 104, 182103	3.4	41
245	High conductive gate leakage current channels induced by In segregation around screw- and mixed-type threading dislocations in lattice-matched In <sub>x</sub> Al <sub>1-x</sub> N/GaN heterostructures. <i>Applied Physics Letters</i> , <b>2010</b> , 97, 232106	3.4	41
244	Growth of high quality and uniformity AlGa <sub>x</sub> N/GaN heterostructures on Si substrates using a single AlGa <sub>x</sub> N layer with low Al composition. <i>Scientific Reports</i> , <b>2016</b> , 6, 23020	4.9	39
243	Influence of strain on the band gap energy of wurtzite InN. <i>Physica Status Solidi (B): Basic Research</i> , <b>2009</b> , 246, 1177-1180	1.3	39
242	InN thin film lattice dynamics by grazing incidence inelastic x-ray scattering. <i>Physical Review Letters</i> , <b>2011</b> , 106, 205501	7.4	38
241	Molecular Beam Epitaxy Growth of Single-Domain and High-Quality ZnO Layers on Nitrided (0001) Sapphire Surface. <i>Japanese Journal of Applied Physics</i> , <b>2003</b> , 42, L99-L101	1.4	38
240	High mobility AlGa <sub>x</sub> N/GaN heterostructures grown on Si substrates using a large lattice-mismatch induced stress control technology. <i>Applied Physics Letters</i> , <b>2015</b> , 106, 142106	3.4	37

239	High-temperature annealing induced evolution of strain in AlN epitaxial films grown on sapphire substrates. <i>Applied Physics Letters</i> , <b>2019</b> , 114, 112105	3.4	36
238	Epitaxy of Single-Crystalline GaN Film on CMOS-Compatible Si(100) Substrate Buffered by Graphene. <i>Advanced Functional Materials</i> , <b>2019</b> , 29, 1905056	15.6	33
237	Tunable surface electron spin splitting with electric double-layer transistors based on InN. <i>Nano Letters</i> , <b>2013</b> , 13, 2024-9	11.5	33
236	Rashba and Dresselhaus spin-orbit coupling in GaN-based heterostructures probed by the circular photogalvanic effect under uniaxial strain. <i>Applied Physics Letters</i> , <b>2010</b> , 97, 181904	3.4	32
235	Sec-Eliminating the SARS-CoV-2 by AlGaIn Based High Power Deep Ultraviolet Light Source. <i>Advanced Functional Materials</i> , <b>2020</b> , 31, 2008452	15.6	32
234	Polarity inversion in high Mg-doped In-polar InN epitaxial layers. <i>Applied Physics Letters</i> , <b>2007</b> , 91, 081913	3.4	31
233	Preparation of H <sub>2</sub> and LPG gas sensor. <i>Sensors and Actuators B: Chemical</i> , <b>2002</b> , 84, 95-97	8.5	31
232	Lattice-Polarity-Driven Epitaxy of Hexagonal Semiconductor Nanowires. <i>Nano Letters</i> , <b>2016</b> , 16, 1328-34	11.5	30
231	ZnO thin film grown on silicon by metal-organic chemical vapor deposition. <i>Journal of Crystal Growth</i> , <b>2002</b> , 243, 13-18	1.6	30
230	Deep Ultraviolet Light Source from Ultrathin GaN/AlN MQW Structures with Output Power Over 2 Watt. <i>Advanced Optical Materials</i> , <b>2019</b> , 7, 1801763	8.1	29
229	Advances in InN epitaxy and its material control by MBE towards novel InN-based QWs. <i>Journal of Crystal Growth</i> , <b>2009</b> , 311, 2073-2079	1.6	29
228	k-space imaging of anisotropic 2D electron gas in GaN/GaAlN high-electron-mobility transistor heterostructures. <i>Nature Communications</i> , <b>2018</b> , 9, 2653	17.4	28
227	The origin and evolution of V-defects in In <sub>x</sub> Al <sub>1-x</sub> N epilayers grown by metalorganic chemical vapor deposition. <i>Applied Physics Letters</i> , <b>2009</b> , 95, 231909	3.4	27
226	Temperature-controlled epitaxy of In <sub>x</sub> Ga <sub>1-x</sub> N alloys and their band gap bowing. <i>Journal of Applied Physics</i> , <b>2011</b> , 110, 113514	2.5	27
225	Influence of annealing on ZnO thin film grown by plasma-assisted MOCVD. <i>Vacuum</i> , <b>2003</b> , 69, 473-476	3.7	27
224	Unambiguous Identification of Carbon Location on the N Site in Semi-insulating GaN. <i>Physical Review Letters</i> , <b>2018</b> , 121, 145505	7.4	27
223	Elastically frustrated rehybridization: Origin of chemical order and compositional limits in InGaIn quantum wells. <i>Physical Review Materials</i> , <b>2018</b> , 2,	3.2	26
222	High quality AlN epilayers grown on nitrided sapphire by metal organic chemical vapor deposition. <i>Scientific Reports</i> , <b>2017</b> , 7, 42747	4.9	25

221	Photoluminescence and pressure effects in short period InN/nGaN superlattices. <i>Journal of Applied Physics</i> , <b>2013</b> , 113, 123101	2.5	25
220	Search for free holes in InN:Mg-interplay between surface layer and Mg-acceptor doped interior. <i>Journal of Applied Physics</i> , <b>2009</b> , 105, 123713	2.5	25
219	Performance enhancement mechanisms of passivated InN/GaN-heterostructured ion-selective field-effect-transistor pH sensors. <i>Sensors and Actuators B: Chemical</i> , <b>2013</b> , 181, 810-815	8.5	24
218	Anomalous Hall mobility kink observed in Mg-doped InN: Demonstration of p-type conduction. <i>Applied Physics Letters</i> , <b>2010</b> , 97, 222114	3.4	24
217	Hole mobility in wurtzite InN. <i>Applied Physics Letters</i> , <b>2011</b> , 98, 192114	3.4	24
216	Effect of electron distribution in InN films on infrared reflectance spectrum of longitudinal optical phonon-plasmon interaction region. <i>Journal of Applied Physics</i> , <b>2008</b> , 103, 053515	2.5	24
215	Effect of Mg doping on enhancement of terahertz emission from InN with different lattice polarities. <i>Applied Physics Letters</i> , <b>2010</b> , 96, 061907	3.4	23
214	Vacancy-type defects in Mg-doped InN probed by means of positron annihilation. <i>Journal of Applied Physics</i> , <b>2009</b> , 105, 054507	2.5	23
213	Residual stress in AlN films grown on sapphire substrates by molecular beam epitaxy. <i>Superlattices and Microstructures</i> , <b>2016</b> , 93, 27-31	2.8	23
212	Repeatable Room Temperature Negative Differential Resistance in AlN/GaN Resonant Tunneling Diodes Grown on Sapphire. <i>Advanced Electronic Materials</i> , <b>2019</b> , 5, 1800651	6.4	23
211	Realization of low dislocation density AlN on a small-coalescence-area nano-patterned sapphire substrate. <i>CrystEngComm</i> , <b>2019</b> , 21, 2490-2494	3.3	22
210	Large-Scale Synthesis and Systematic Photoluminescence Properties of Monolayer MoS <sub>2</sub> on Fused Silica. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2016</b> , 8, 18570-6	9.5	22
209	Fabrication and properties of coherent-structure In-polarity In <sub>0.7</sub> Ga <sub>0.3</sub> N multiquantum wells emitting at around 1.55 $\mu$ m. <i>Journal of Applied Physics</i> , <b>2007</b> , 102, 083539	2.5	22
208	Graphene-Assisted Epitaxy of Nitrogen Lattice Polarity GaN Films on Non-Polar Sapphire Substrates for Green Light Emitting Diodes. <i>Advanced Functional Materials</i> , <b>2020</b> , 30, 2001283	15.6	21
207	Performance improvement of AlGaIn-based deep-ultraviolet light-emitting diodes by inserting single spike barriers. <i>Superlattices and Microstructures</i> , <b>2016</b> , 100, 941-946	2.8	21
206	Crystal quality evolution of AlN films via high-temperature annealing under ambient N <sub>2</sub> conditions. <i>CrystEngComm</i> , <b>2018</b> , 20, 6613-6617	3.3	21
205	Vacancy-type defects in In <sub>x</sub> Ga <sub>1-x</sub> N alloys probed using a monoenergetic positron beam. <i>Journal of Applied Physics</i> , <b>2012</b> , 112, 014507	2.5	20
204	Infrared analysis of hole properties of Mg-doped p-type InN films. <i>Applied Physics Letters</i> , <b>2008</b> , 93, 231903	3.3	20

203	Growth of In-polar and N-polar InN nanocolumns on GaN templates by molecular beam epitaxy. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2006</b> , 3, 1561-1565		20
202	Mechanism of stress-driven composition evolution during hetero-epitaxy in a ternary AlGaIn system. <i>Scientific Reports</i> , <b>2016</b> , 6, 25124	4.9	20
201	Tuning the graphene work function by uniaxial strain. <i>Applied Physics Letters</i> , <b>2015</b> , 106, 043106	3.4	19
200	Origin of Improved Optical Quality of Monolayer Molybdenum Disulfide Grown on Hexagonal Boron Nitride Substrate. <i>Small</i> , <b>2016</b> , 12, 198-203	11	19
199	Infrared to vacuum-ultraviolet ellipsometry and optical Hall-effect study of free-charge carrier parameters in Mg-doped InN. <i>Journal of Applied Physics</i> , <b>2013</b> , 113, 013502	2.5	19
198	Revealing of the transition from n- to p-type conduction of InN:Mg by photoconductivity effect measurement. <i>Scientific Reports</i> , <b>2014</b> , 4, 4371	4.9	19
197	Broadening factors of E1(LO) phonon-plasmon coupled modes of hexagonal InN investigated by infrared reflectance measurements. <i>Physical Review B</i> , <b>2007</b> , 76,	3.3	19
196	High-electron-mobility InN epilayers grown on silicon substrate. <i>Applied Physics Letters</i> , <b>2018</b> , 112, 162102	9.4	18
195	Identifying a doping type of semiconductor nanowires by photoassisted kelvin probe force microscopy as exemplified for GaN nanowires. <i>Optical Materials Express</i> , <b>2017</b> , 7, 904	2.6	17
194	Temperature sensitive photoconductivity observed in InN layers. <i>Applied Physics Letters</i> , <b>2013</b> , 102, 072102	3.4	17
193	Strain effects on In <sub>x</sub> Al <sub>1-x</sub> N crystalline quality grown on GaN templates by metalorganic chemical vapor deposition. <i>Journal of Applied Physics</i> , <b>2010</b> , 107, 043515	2.5	17
192	Electronic structure of GaInN semiconductors investigated by x-ray absorption spectroscopy. <i>Applied Physics Letters</i> , <b>2011</b> , 98, 181901	3.4	17
191	Shear strain induced modulation to the transport properties of graphene. <i>Applied Physics Letters</i> , <b>2014</b> , 105, 083108	3.4	16
190	Free and bound excitonic effects in Al <sub>0.5</sub> Ga <sub>0.5</sub> N/Al <sub>0.35</sub> Ga <sub>0.65</sub> N MQWs with different Si-doping levels in the well layers. <i>Scientific Reports</i> , <b>2015</b> , 5, 13046	4.9	16
189	Effect of injection current on the optical polarization of AlGaIn-based ultraviolet light-emitting diodes. <i>Optics Express</i> , <b>2014</b> , 22, 19589-94	3.3	16
188	Observation of the photoinduced anomalous Hall effect in GaN-based heterostructures. <i>Applied Physics Letters</i> , <b>2011</b> , 98, 122104	3.4	16
187	Structural and optical properties of ZnO film by plasma-assisted MOCVD. <i>Optical and Quantum Electronics</i> , <b>2002</b> , 34, 883-891	2.4	16
186	Single-photon emission from a further confined InGaIn/GaN quantum disc via reverse-reaction growth. <i>Quantum Engineering</i> , <b>2019</b> , 1, e20	4.5	15

185	Experimental Evidence of Large Bandgap Energy in Atomically Thin AlN. <i>Advanced Functional Materials</i> , <b>2019</b> , 29, 1902608	15.6	15
184	Effect of Mg doping on the structural and free-charge carrier properties of InN films. <i>Journal of Applied Physics</i> , <b>2014</b> , 115, 163504	2.5	15
183	Strong circular photogalvanic effect in ZnO epitaxial films. <i>Applied Physics Letters</i> , <b>2010</b> , 97, 041907	3.4	15
182	Terahertz electroluminescence of surface plasmons from nanostructured InN layers. <i>Applied Physics Letters</i> , <b>2010</b> , 96, 183106	3.4	15
181	Lattice-Symmetry-Driven Epitaxy of Hierarchical GaN Nanotripods. <i>Advanced Functional Materials</i> , <b>2017</b> , 27, 1604854	15.6	14
180	Excitonic localization at macrostep edges in AlGa <sub>x</sub> In <sub>1-x</sub> N multiple quantum wells. <i>Superlattices and Microstructures</i> , <b>2017</b> , 104, 397-401	2.8	14
179	High performance of AlGa <sub>x</sub> In <sub>1-x</sub> N deep-ultraviolet light emitting diodes due to improved vertical carrier transport by delta-accelerating quantum barriers. <i>Applied Physics Letters</i> , <b>2019</b> , 114, 172105	3.4	14
178	High-Mobility Two-Dimensional Electron Gas at InGa <sub>x</sub> N <sub>1-x</sub> Heterointerface Grown by Molecular Beam Epitaxy. <i>Advanced Science</i> , <b>2018</b> , 5, 1800844	13.6	14
177	Demonstration of epitaxial growth of strain-relaxed GaN films on graphene/SiC substrates for long wavelength light-emitting diodes. <i>Light: Science and Applications</i> , <b>2021</b> , 10, 117	16.7	14
176	Evidence of type-II band alignment in III-nitride semiconductors: experimental and theoretical investigation for In <sub>0.17</sub> Al <sub>0.83</sub> N/GaN heterostructures. <i>Scientific Reports</i> , <b>2014</b> , 4, 6521	4.9	13
175	Local surface plasmon enhanced polarization and internal quantum efficiency of deep ultraviolet emissions from AlGa <sub>x</sub> In <sub>1-x</sub> N-based quantum wells. <i>Scientific Reports</i> , <b>2017</b> , 7, 2358	4.9	13
174	Multi-bands photoconductive response in AlGa <sub>x</sub> In <sub>1-x</sub> N/GaN multiple quantum wells. <i>Applied Physics Letters</i> , <b>2014</b> , 104, 172108	3.4	13
173	Anomalous linear photogalvanic effect observed in a GaN-based two-dimensional electron gas. <i>Physical Review B</i> , <b>2011</b> , 84,	3.3	13
172	Anisotropic damping of longitudinal optical phonon-plasmon coupling modes of InN films. <i>Applied Physics Letters</i> , <b>2008</b> , 92, 251901	3.4	13
171	Effect of Precise Control of V/III Ratio on In-Rich InGa <sub>x</sub> N Epitaxial Growth. <i>Japanese Journal of Applied Physics</i> , <b>2006</b> , 45, L1259-L1262	1.4	13
170	In situ spectroscopic ellipsometry in plasma-assisted molecular beam epitaxy of InN under different surface stoichiometries. <i>Journal of Applied Physics</i> , <b>2006</b> , 99, 044913	2.5	13
169	Exciton emission of quasi-2D InGa <sub>x</sub> N in GaN matrix grown by molecular beam epitaxy. <i>Scientific Reports</i> , <b>2017</b> , 7, 46420	4.9	12
168	Molecular beam epitaxy of single-crystalline aluminum film for low threshold ultraviolet plasmonic nanolasers. <i>Applied Physics Letters</i> , <b>2018</b> , 112, 231904	3.4	12

167	Electronic properties of polycrystalline graphene under large local strain. <i>Applied Physics Letters</i> , <b>2014</b> , 104, 243108	3.4	12
166	Lattice polarity detection of InN by circular photogalvanic effect. <i>Applied Physics Letters</i> , <b>2009</b> , 95, 031902	3.4	12
165	Two-step growth of ZnO thin films on diamond/Si by low-pressure metal-organic chemical vapour deposition. <i>Journal Physics D: Applied Physics</i> , <b>2002</b> , 35, L74-L76	3	12
164	Elastic properties of indium nitrides grown on sapphire substrates determined by nano-indentation: In comparison with other nitrides. <i>AIP Advances</i> , <b>2015</b> , 5, 077131	1.5	11
163	Intersubband transitions at atmospheric window in Al <sub>x</sub> Ga <sub>1-x</sub> N/GaN multiple quantum wells grown on GaN/sapphire templates adopting AlN/GaN superlattices interlayer. <i>Applied Physics Letters</i> , <b>2011</b> , 98, 132105	3.4	11
162	Abnormal magnetic-field dependence of Hall coefficient in InN epilayers. <i>Applied Physics Letters</i> , <b>2009</b> , 95, 012107	3.4	11
161	Deep donor state in InN: Temperature-dependent electron transport in the electron accumulation layers and its influence on Hall-effect measurements. <i>Applied Physics Letters</i> , <b>2011</b> , 99, 182107	3.4	11
160	Identification of the main contributions to the conductivity of epitaxial InN. <i>Physical Review B</i> , <b>2011</b> , 84,	3.3	11
159	Cathodoluminescence Study on Spatial Luminescence Properties of InN/GaN Multiple Quantum Wells Consisting of 1-Monolayer-Thick InN Wells/GaN Matrix. <i>Journal of Electronic Materials</i> , <b>2008</b> , 37, 597-602	1.9	11
158	Hexagonal BN-Assisted Epitaxy of Strain Released GaN Films for True Green Light-Emitting Diodes. <i>Advanced Science</i> , <b>2020</b> , 7, 2000917	13.6	11
157	Single-photon emission from isolated monolayer islands of InGaN. <i>Light: Science and Applications</i> , <b>2020</b> , 9, 159	16.7	11
156	EGa <sub>2</sub> O <sub>3</sub> thin film grown on sapphire substrate by plasma-assisted molecular beam epitaxy. <i>Journal of Semiconductors</i> , <b>2019</b> , 40, 012802	2.3	11
155	Repeatable asymmetric resonant tunneling in AlGa <sub>N</sub> /Ga <sub>N</sub> double barrier structures grown on sapphire. <i>Applied Physics Letters</i> , <b>2019</b> , 114, 073503	3.4	10
154	Intersubband Transition in GaN/InGa <sub>N</sub> Multiple Quantum Wells. <i>Scientific Reports</i> , <b>2015</b> , 5, 11485	4.9	10
153	Al diffusion at AlN/Si interface and its suppression through substrate nitridation. <i>Applied Physics Letters</i> , <b>2020</b> , 116, 232105	3.4	10
152	Strain effect on the optical polarization properties of c-plane Al <sub>0.3</sub> Ga <sub>0.7</sub> N/GaN superlattices. <i>Optics Express</i> , <b>2014</b> , 22, 6322-8	3.3	10
151	Effect of polarization on intersubband transition in AlGa <sub>N</sub> /Ga <sub>N</sub> multiple quantum wells. <i>Applied Physics Letters</i> , <b>2013</b> , 102, 192109	3.4	10
150	Effect of GaN interlayer on polarity control of epitaxial ZnO thin films grown by molecular beam epitaxy. <i>Applied Physics Letters</i> , <b>2010</b> , 97, 151908	3.4	10



149	Dependence of Mg acceptor levels in InN on doping density and temperature. <i>Journal of Applied Physics</i> , <b>2011</b> , 110, 093505	2.5	10
148	Detection of spin-orbit coupling of surface electron layer via reciprocal spin Hall effect in InN films. <i>Applied Physics Letters</i> , <b>2012</b> , 101, 132404	3.4	10
147	Vacancy-engineering-induced dislocation inclination in III-nitrides on Si substrates. <i>Physical Review Materials</i> , <b>2020</b> , 4,	3.2	10
146	Positive temperature coefficient of photovoltaic efficiency in solar cells based on InGaN/GaN MQWs. <i>Applied Physics Letters</i> , <b>2016</b> , 109, 062104	3.4	10
145	High-quality AlN epitaxy on sapphire substrates with sputtered buffer layers. <i>Superlattices and Microstructures</i> , <b>2017</b> , 105, 34-38	2.8	9
144	Study on AlGaN P-I-N-I-N solar-blind avalanche photodiodes with Al <sub>0.45</sub> Ga <sub>0.55</sub> N multiplication layer. <i>Electronic Materials Letters</i> , <b>2015</b> , 11, 1053-1058	2.9	9
143	Effect of Grain Boundary Scattering on Electron Mobility of N-Polarity InN Films. <i>Applied Physics Express</i> , <b>2013</b> , 6, 021001	2.4	9
142	Determination of the surface band bending in In Ga N films by hard x-ray photoemission spectroscopy. <i>Science and Technology of Advanced Materials</i> , <b>2013</b> , 14, 015007	7.1	9
141	Ionic liquid gated electric-double-layer transistors based on Mg-doped InN epitaxial films. <i>Applied Physics Letters</i> , <b>2013</b> , 103, 253508	3.4	9
140	In situ spectroscopic ellipsometry and RHEED monitored growth of InN nanocolumns by molecular beam epitaxy. <i>Journal of Crystal Growth</i> , <b>2007</b> , 301-302, 496-499	1.6	9
139	Greatly enhanced performance of AlGaN-based deep ultraviolet light emitting diodes by introducing a polarization modulated electron blocking layer. <i>Optics Express</i> , <b>2019</b> , 27, A1458-A1466	3.3	9
138	Thermally annealed wafer-scale h-BN films grown on sapphire substrate by molecular beam epitaxy. <i>Applied Physics Letters</i> , <b>2020</b> , 116, 142104	3.4	9
137	Performance improvement of AlGaN-based deep-ultraviolet light-emitting diodes via asymmetric step-like AlGaN quantum wells. <i>Superlattices and Microstructures</i> , <b>2017</b> , 104, 240-246	2.8	8
136	Single photon source based on an InGaN quantum dot in a site-controlled optical horn structure. <i>Applied Physics Letters</i> , <b>2019</b> , 115, 022101	3.4	8
135	Formation of p-n-p junction with ionic liquid gate in graphene. <i>Applied Physics Letters</i> , <b>2014</b> , 104, 143102	3.4	8
134	Large magnetoresistance effect in InN epilayers. <i>Physical Review B</i> , <b>2010</b> , 82,	3.3	8
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128	Correlation between switching to n-type conductivity and structural defects in highly Mg-doped InN. <i>Applied Physics Letters</i> , <b>2015</b> , 106, 232102	3.4	7
127	Controlled bunching approach for achieving high efficiency active region in AlGaIn-based deep ultraviolet light-emitting devices with dual-band emission. <i>Applied Physics Letters</i> , <b>2020</b> , 116, 212102	3.4	7
126	Vertical leakage induced current degradation and relevant traps with large lattice relaxation in AlGaIn/GaN heterostructures on Si. <i>Applied Physics Letters</i> , <b>2018</b> , 112, 032104	3.4	7
125	Carrier recombination processes in In-polar n-InN in regions of low residual electron density. <i>Journal of Applied Physics</i> , <b>2009</b> , 106, 113515	2.5	7
124	Carrier recombination processes in Mg-doped N-polar InN films. <i>Applied Physics Letters</i> , <b>2011</b> , 98, 181908	3.4	7
123	Coexistence of free holes and electrons in InN:Mg with In- and N-growth polarities. <i>Journal of Applied Physics</i> , <b>2012</b> , 111, 093719	2.5	7
122	Influence of high-energy local orbitals and electron-phonon interactions on the band gaps and optical absorption spectra of hexagonal boron nitride. <i>Physical Review B</i> , <b>2020</b> , 102,	3.3	7
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120	Growth of high quality n-Al 0.5 Ga 0.5 N thick films by MOCVD. <i>Materials Letters</i> , <b>2016</b> , 176, 298-300	3.3	7
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98	Individually resolved luminescence from closely stacked GaN/AlN quantum wells. <i>Photonics Research</i> , <b>2020</b> , 8, 610	6	5
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